/ Descriptions

TO-220AC

Ultrafast Recovery Diode in a TO-220AC Plastic Package.

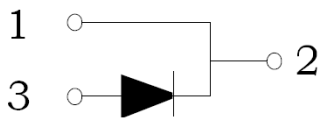
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

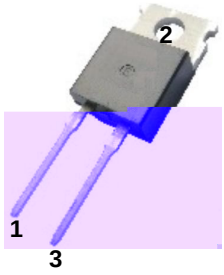
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

/ Equivalent Circuit



/ Pinning



PIN1 2 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Maximum Average Forward Current	I_F	1 30	A
Peak forward surge current	I_{FSM}	300	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.8	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

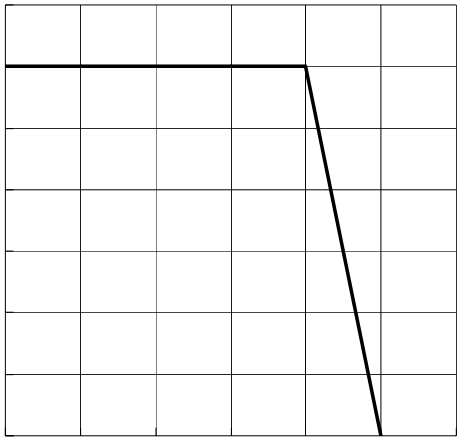
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=5.0A T_C=25			1.35	V
		I_F=5.0A T_C=150			1.15	
		I_F=30A T_C=25			1.65	
		I_F=30A T_C=150			1.25	
Instantaneous Reverse Current Note1	I_R	V_R=600V T_a=25			0.25	mA
		V_R=420V T_a=150			1	
		V_R=600V T_a=150			2	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			50	ns

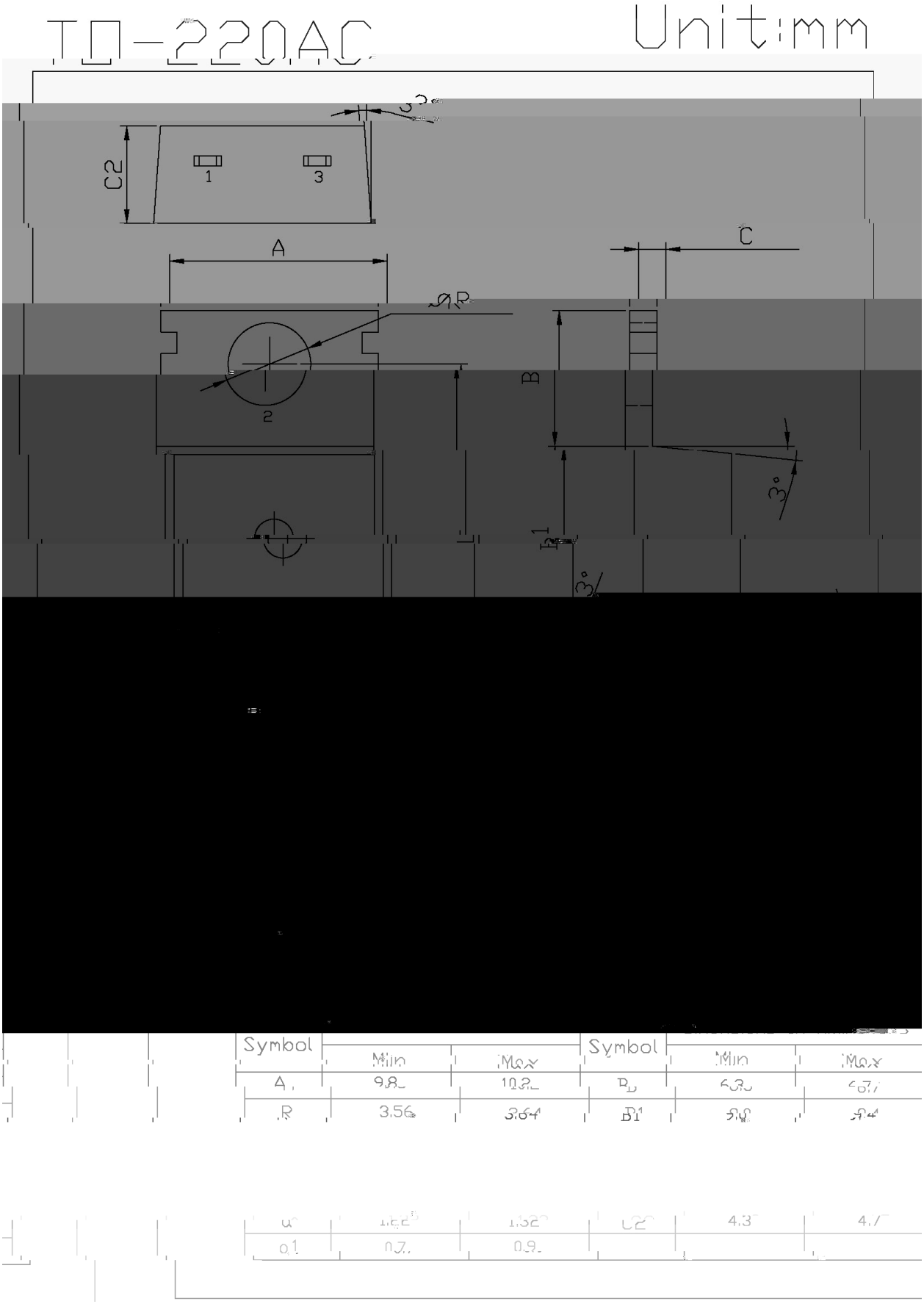
/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Un5gss otherwise noted, values for the parameters of a single chip

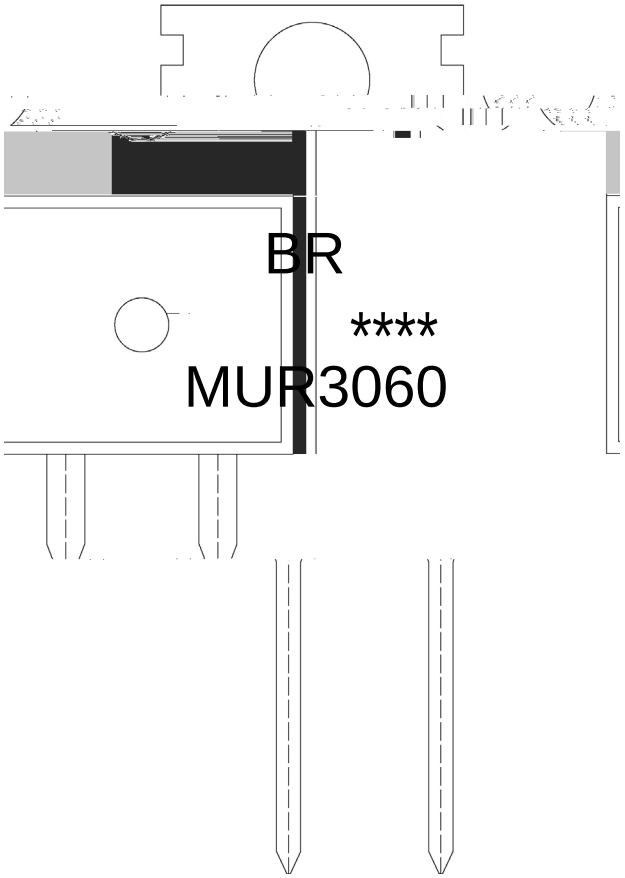
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

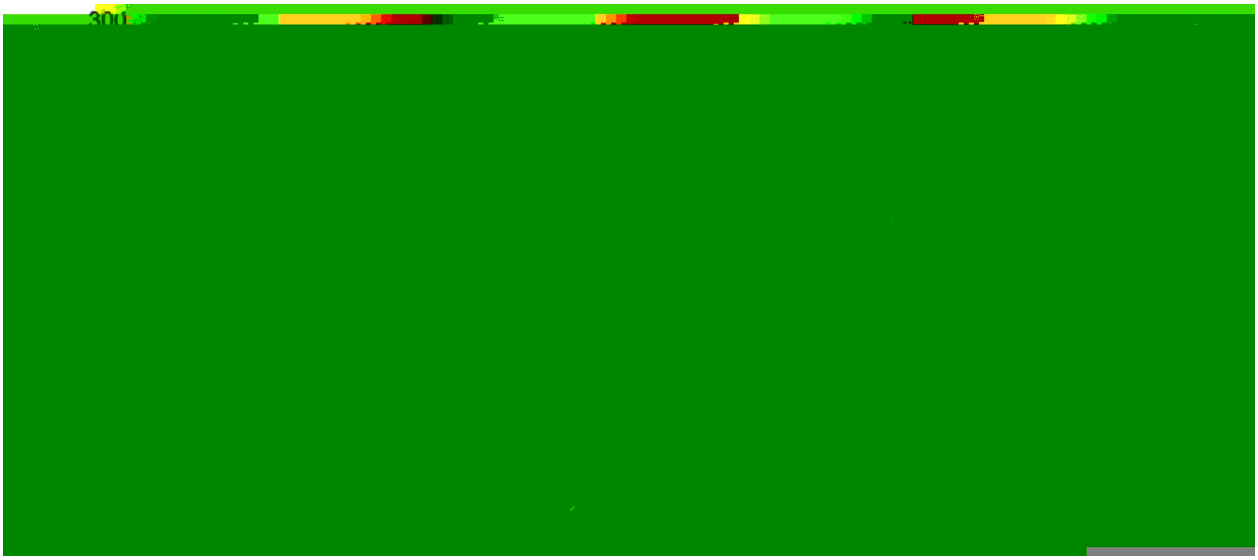
MUR3060

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Note:

BR:	Company Code
MUR3060	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1		25 150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3			2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units			Dimension (unit mm³)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	

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